

### N-Channel Super Junction Power MOSFET III

### **General Description**

The series of devices use advanced trench gate super junction technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

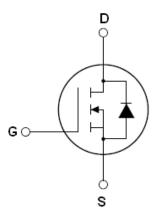
#### **Features**

- New technology for high voltage device
- Low on-resistance and low conduction losses
- small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### **Application**

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

V <sub>DS</sub>	650	V
R <sub>DS(ON)TYP</sub>	290	mΩ
$I_{\mathrm{D}}$	11.5	A



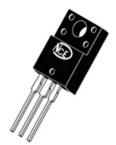
Schematic diagram

### **Package Marking And Ordering Information**

Device	Device Package	Marking
NCE65T360D	TO-263	NCE65T360D
NCE65T360	TO-220	NCE65T360
NCE65T360F	TO-220F	NCE65T360F







TO-263

TO-220

**TO-220F** 

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Table 1. Absolute Maximum Ratings (T<sub>c</sub>=25℃)

Parameter	Symbol	NCE65T360D NCE65T360	NCE65T360F	Unit
Drain-Source Voltage (VGS=0V)	V <sub>DS</sub>	65	50	V
Gate-Source Voltage (V <sub>DS</sub> =0V), AC(f>1HZ)	V <sub>G</sub> s	土	30	V
Continuous Drain Current at T <sub>C</sub> =25°C	I <sub>D (DC)</sub>	11.5	11.5*	Α
Continuous Drain Current at T <sub>C</sub> =100°C	I <sub>D (DC)</sub>	7	7*	Α
Pulsed drain current (Note 1)	I <sub>DM (pluse)</sub>	46	46*	Α
Maximum Power Dissipation(T <sub>C</sub> =25℃)	P <sub>D</sub>	101	32.6	W
Derate above 25°C		0.81	0.26	w/°C
Single pulse avalanche energy (Note2)	Eas	144		mJ
Avalanche current <sup>(Note 1)</sup>	I <sub>AR</sub>	6		Α
Repetitive Avalanche energy , $t_{AR}$ limited by $T_{jmax}$ (Note 1)	E <sub>AR</sub>	0.5		mJ

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Parameter	Symbol	NCE65T360D NCE65T360	NCE65T360F	Unit
Drain Source voltage slope, V <sub>DS</sub> ≤480 V,	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} \leq 480 \text{ V,I}_{SD} < I_{D}$	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55	+150	°C

<sup>\*</sup> limited by maximum junction temperature

### **Table 2. Thermal Characteristic**

Parameter	Symbol	NCE65T360D NCE65T360	NCE65T360F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R <sub>thJC</sub>	1.24	3.83	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R <sub>thJA</sub>	62	80	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

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Parameter	Symbol	Condition	Min	Тур	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V,V <sub>GS</sub> =0V		0.05	1	μΑ
Zero Gate Voltage Drain Current(Tc=125℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V,V <sub>GS</sub> =0V			100	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	3	3.5	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A		290	360	mΩ
Dynamic Characteristics						
Input Capacitance	C <sub>lss</sub>	\/ 50\/\/ 0\/		870		pF
Output Capacitance	Coss	$V_{DS}$ =50V, $V_{GS}$ =0V, F=1.0MHz		54		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UMHZ		1.8		pF
Total Gate Charge	$Q_g$	\/ 400\/   44.54		19		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =480V,I <sub>D</sub> =11.5A, V <sub>GS</sub> =10V		6		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V		6.5		nC
Switching times						
Turn-on Delay Time	t <sub>d(on)</sub>			11		nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =380V, $I_{D}$ =5.5A,		8		nS
Turn-Off Delay Time	$t_{d(off)}$	$R_G=3\Omega,V_{GS}=10V$		58	70	nS
Turn-Off Fall Time	t <sub>f</sub>			9	14	nS
Source- Drain Diode Characteristics	-					
Source-drain current(Body Diode)	I <sub>SD</sub>	T 05°0			11.5	Α
Pulsed Source-drain current(Body Diode)	I <sub>SDM</sub>	T <sub>C</sub> =25°C			46	Α
Forward on voltage	V <sub>SD</sub>	Tj=25°C,I <sub>SD</sub> =11.5A,V <sub>GS</sub> =0V		0.9	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	T:-05°C   5.04		220		nS
Reverse Recovery Charge	Q <sub>rr</sub>	Tj=25°C,I <sub>F</sub> =5.8A,		2.2		uC
Peak Reverse Recovery Current	I <sub>rrm</sub>	di/dt=100A/µs		19		Α

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

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<sup>2.</sup> Tj=25°C,VDD=50V,VG=10V, R<sub>G</sub>=25 $\Omega$ 



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

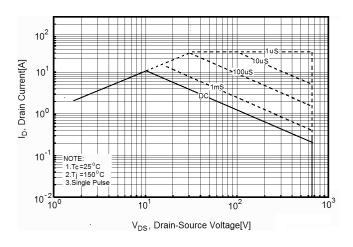


Figure 2. Safe operating area for TO-220F

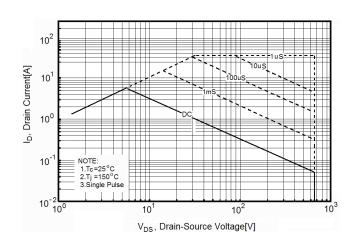


Figure 3. Source-Drain Diode Forward Voltage

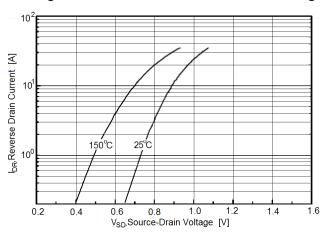


Figure 4. Output characteristics

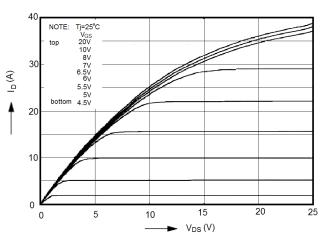


Figure 5. Transfer characteristics

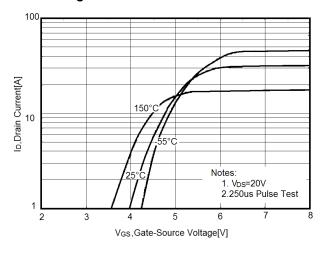
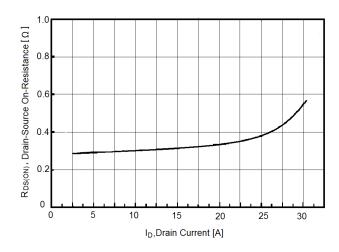


Figure 6. Static drain-source on resistance



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Figure 7. R<sub>DS(ON)</sub> vs Junction Temperature

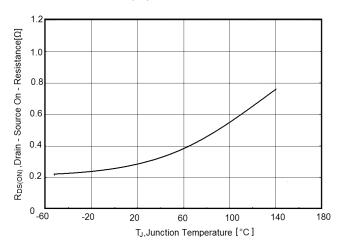


Figure8. BV<sub>DSS</sub> vs Junction Temperature

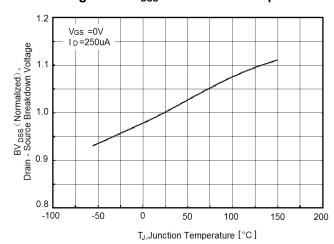


Figure 9. Maximum ID vs Junction Temperature

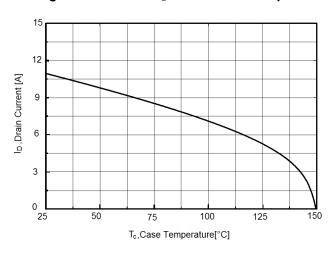


Figure 10. Gate charge waveforms

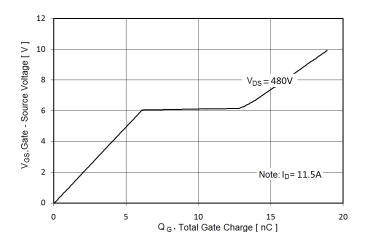


Figure11. Capacitance

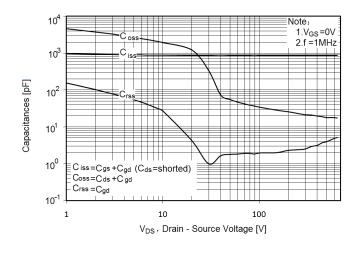
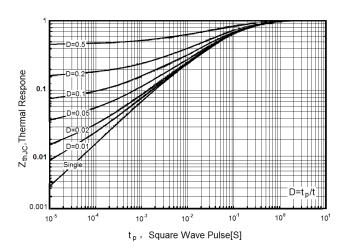


Figure 12. Transient Thermal Impedance

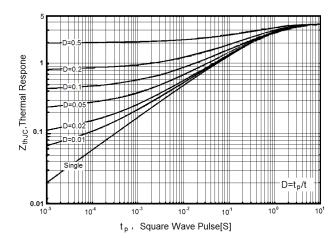


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Figure 13. Transient Thermal Impedance for TO-220F

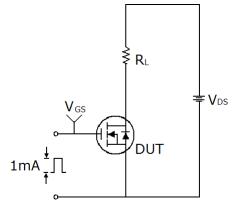


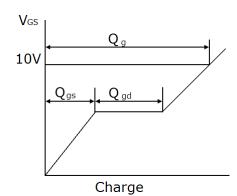
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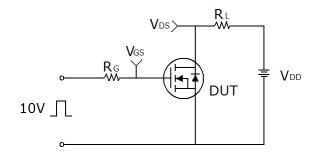
### **Test circuit**

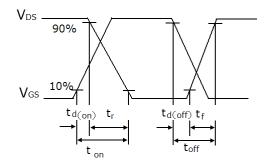
### 1) Gate charge test circuit & Waveform



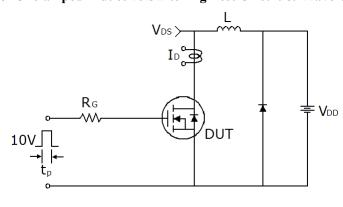


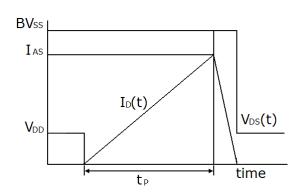
### 2) Switch Time Test Circuit:





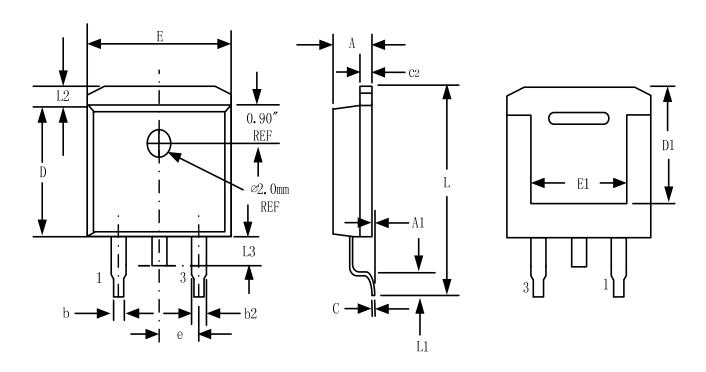
### 3) Unclamped Inductive Switching Test Circuit & Waveforms







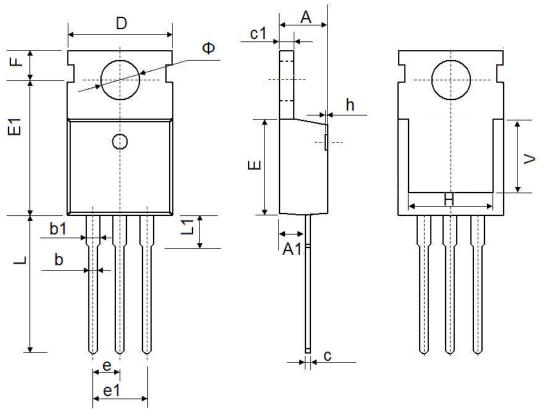
# **TO-263-3L Package Information**



Sumb al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.32	4.57	0.170	0.180	
A1	-	0.25		0.010	
b	0.71	0.94	0.028	0.037	
b2	1.15	1.40	0.045	0.055	
С	0.46	0.61	0.018	0.024	
c2	1.22	1.40	0.048	0.055	
D	8.89	9.40	0.350	0.370	
D1	8.01	8.23	0.315	0.324	
E	10.04	10.28	0.395	0.405	
E1	7.88	8.08	0.310	0.318	
е	2.54	BSC	0.100	) BSC	
L	14.73	15.75	0.580	0.620	
L1	2.29	2.79	0.090	0.110	
L2	1.15	1.39	0.045	0.055	
L3	1.27	1.77	0.050	0.070	



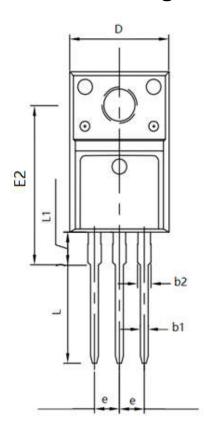
# **TO-220-3L-C Package Information**

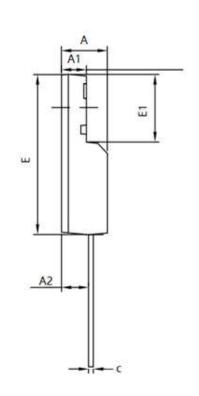


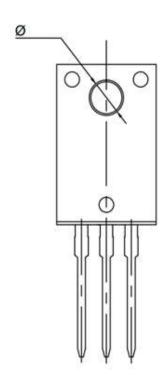
Commela a l	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500	REF.	0.295	REF.	
Ф	3.400	3.800	0.134	0.150	



# **TO-220F Package Information**







Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.500	4.900	0.177	0.193	
A1	2.340	2.740	0.092	0.108	
A2	2.560	2.960	0.101	0.117	
b1	0.700	0.900	0.028	0.035	
b2	1.180	1.580	0.046	0.062	
С	0.400	0.600	0.016	0.024	
D	9.960	10.360	0.392	0.408	
E	15.670	15.970	0.617	0.629	
E1	6.500	6.900	0.256	0.272	
E2	15.500	16.100	0.610	0.634	
е	2.540	) TYP	0.100	) TYP	
Ф	3.080	3.280	0.121	0.129	
L	12.640	13.240	0.498	0.521	
L1	3.030	3.430	0.119	0.135	



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